



IEEE Electron Devices Society Newsletter

January 1996
 Vol. 3, No. 1 ISSN:1074 1879
 Editor: Krishna Shenai

Table of Contents

Upcoming Technical Meetings	1
• 1996 SIMC	
• 1996 MCMC	
• 1996 ICMTS	
• 1996 IPRM	
A Message from the Editor	2
Society News	7
• A Message from the Outgoing President	
• EDS Members Named Winners of 1996 IEEE Field Awards	
• EDS Announces an "All Electronic" Journal	
Regional & Chapter News	10
• USA, Canada & Latin America	
• Europe, Middle East & Africa	
• Asia & Pacific	
EDS Meetings Calendar	17
Eastern Europe Library Project	19
Newsletter Editorial Staff	20

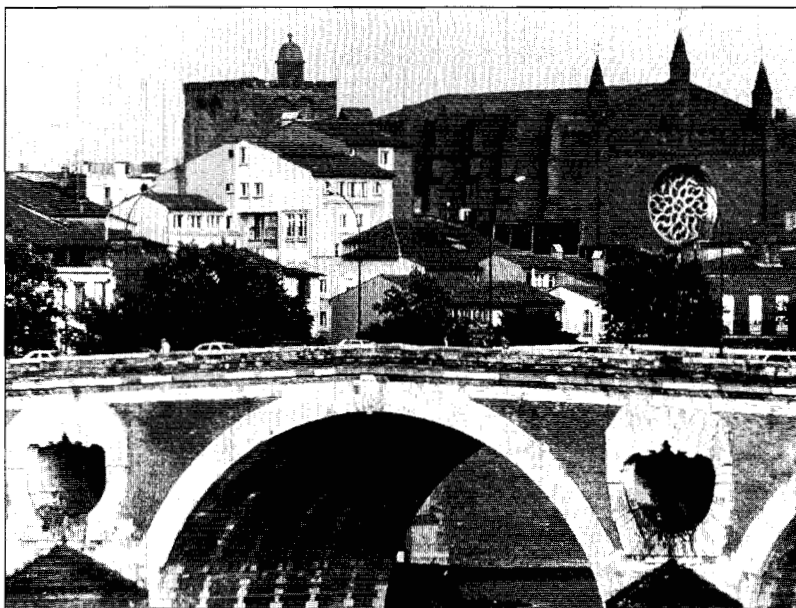
Contributions Welcome

Readers are encouraged to submit news items concerning the Society and its members. Please send your ideas/articles directly to either the Editor or appropriate Associate Editor. All contact information is listed on the back cover page. Whenever possible, e-mail is the preferred form of submittal.

Newsletter Deadlines

<u>Issue</u>	<u>Due Date</u>
January	October 1st
April	January 1st
July	April 1st
October	July 1st

1996 IEEE Semiconducting and Semi-Insulating Materials Conference (SIMC9)



The 9th IEEE Semiconducting and Semi-Insulating Materials Conference (SIMC9) will be held April 29-May 3, 1996 at the Atria-Mercure Hotel Center in Toulouse, France. The Atria is located in the center of the town within easy walking distance from many historical sites such as the Capitol, Saint Sernin basilic and the Jacobin church.

Half-way between Portugal and Germany, between the Atlantic Ocean and the Mediterranean Sea, capital of Midi-Pyrénées region, Toulouse plays an important role in France and abroad. Internationally acknowledged as a leader in technology, Toulouse has retained all the richness of its past; visitors appreciate its picturesque streets, public buildings, lively terrace cafés, a stroll along the banks of the Garonne river... A town teeming with history, life and culture. Toulouse is already in step with the 21st century: advanced aeronautics with Concorde and Airbus, European centre for the aerospace industry with the development of the Ariane launcher and satellites, scientific universities, "grandes écoles", research laboratories... Toulouse has become a city for top scientists. City of the "Capitouls", embellished by the Renaissance Arts, Toulouse has always been at the forefront of French life and thought. Its rich,

(continued on page 3)

Your Comments Solicited

Your comments and suggestions are most welcome. Please write directly to the Editor of the Newsletter at the address given on the back cover page.

Upcoming Technical Meetings

SIMC9

(continued from page 1)

tumultuous past has left a great architectural heritage.

The SIMC is a series of biennial conferences initiated in 1980 in Nottingham (UK). SIMC7 was held in Mexico, SIMC8 in Poland and the latter attracted more than 125 delegates from 23 countries. This year it will be held in France and this is good news for those also being receptive to "regional cuisine" and outstanding wines! Previously named the "Semi-Insulating III-V Materials Conference", the title of the conference was changed last year by the IEEE advisory committee in order to open this conference to all the compound semiconducting materials, which are involved in the prospective electronic and photonic devices of nowadays. Clearly, SIMC-9 will bring together specialists from various fields of materials science, solid state physics, device and process engineering. The purpose of this meeting is to discuss growth, characterization, theory, device applications, and materials issues of the III-V semiconductors, which can be rendered insulating by special elaboration procedures or by post-growth treatments, but also of other promising compound materials such as SiGe, GaN, SiC, Participants of the conference will have an opportunity to exchange ideas and to discuss future directions of development of this expanding field. During the conference an exhibition of equipment, materials and services of interest to the materials community will be held in a room adjacent to the amphitheater with coffee at your disposition. The program of the conference will include invited, oral and poster presentations. Proceedings including all accepted contributions will appear as a separate hard-cover book. The book will be sent to the participants of the conference.

Topics to be Emphasized:

Growth — Bulk and epitaxial growth of materials; post-growth treatments; low temperature III-V molecular beam epitaxy (MBE); technology of wide gap materials such as nitrides and of SiGe, SiC, ...; defect control in high purity compounds, and in irradiated materials.

Characterization — Electrical and optical evaluation; deep level analysis;

point and extended defect structure; mapping and uniformity of materials; interface investigations.

Theory — Heat and mass transport in technological processes; surface and interface states; identification of defects and impurities, compensation processes.

Applications — Electronic and optoelectronic devices integrating these materials; the role of point and extended defect; reliability and processing issues.

Abstract submission:

Prospective authors are invited to submit one original and five copies of a one-page abstract. Facsimile copies of abstracts will not be accepted. Abstract must be camera-ready and typed on a A4 (8 1/2" x 11") white paper, with left and right margins of 2 cm. The upper and lower margin should be 2.5 cm and the abstract must include the header containing the title, author's name, affiliation, address and the telephone number, facsimile number and

e-mail address. Remember, **the abstract deadline is January 15, 1996.**

Other important dates:

Notification	February 15, 1996
of Acceptance	
Early registration	March 15, 1996

A social program is planned for participants and accompanying persons. It will include an evening reception party and a visit to Albi, Cordes and other interesting sites.

For more information and/or to be registered, please contact Josiane SUTRA, IEEE-SIMC9 CEMES/CNRS, BP 4347, 31055 Toulouse Cedex France, via FAX : 33 62 25 79 99, or E-mail: simc-9@cemes.cemes.fr

So be sure to register and join the action. See you in April !

— Alain Claverie
General Chairman SIMC-9
CNRS Toulouse

1996 IEEE Multi-Chip Module Conference (MCMC)



The IEEE Multi-Chip Module Conference (MCMC) will be held February 5 - 7, 1996 in Santa Cruz, CA. This multi-disciplinary conference, co-sponsored by four IEEE Societies (Computer, Circuits and Systems, Electron Devices, and Components, Packaging and Manufacturing Technology), covers a wide range of topics in state-of-the-art multichip module

(MCM) analysis, design, technology, and applications. This goal of the conference is to bring together elements of packaging technology and design, circuits and systems design, computer-aided design, modeling, analysis and education. The conference is unique in its multi-disciplinary coverage of all aspects of MCMs,

(continued on page 4)